

**AMENDMENT TO H.R. 5136, AS REPORTED  
OFFERED BY MR. TONKO OF NEW YORK**

Page 79, after line 6, insert the following:

1 **SEC. 244. SENSE OF CONGRESS AFFIRMING THE IMPOR-**  
2 **TANCE OF DEPARTMENT OF DEFENSE PAR-**  
3 **TICIPATION IN DEVELOPMENT OF NEXT GEN-**  
4 **ERATION SEMICONDUCTOR TECHNOLOGIES.**

5 (a) FINDINGS.—Congress makes the following find-  
6 ings:

7 (1) The next generation of weapons systems,  
8 battlefield sensors, and intelligence platforms will  
9 need to be lighter, more agile, consume less power,  
10 and have greater computational power, which can  
11 only be achieved by decreasing the feature size of in-  
12 tegrated circuits to the nanometer scale.

13 (2) There is a growing concern in the Depart-  
14 ment of Defense and the United States intelligence  
15 community over the offshore shift in development  
16 and production of high capacity semiconductors. Re-  
17 liance on providers of semiconductors in the United  
18 States high tech industry will mitigate the security  
19 risks of such an offshore shift.

1           (3) The use of extreme-ultraviolet lithography  
2           (EUVL) is recognized in the semiconductor industry  
3           as critical to the development of the next generation  
4           of integrated circuits.

5           (b) SENSE OF CONGRESS.—It is the sense of Con-  
6           gress that—

7           (1) the United States should establish research  
8           and development facilities to take the lead in pro-  
9           ducing the next generation of integrated circuits;

10          (2) the Department of Defense should support  
11          the establishment of a public-private partnership of  
12          defense laboratory scientists and engineers, univer-  
13          sity researchers, integrated circuit designers and  
14          fabricators, tool manufacturers, material and chem-  
15          ical suppliers, and metrology and inspection tool fab-  
16          ricators to develop extreme-ultraviolet lithography  
17          (EUVL) technologies on 300 micrometer and 450  
18          micrometer wafers; and

19          (3) the targeted feature size of integrated cir-  
20          cuits for EUVL development in the United States  
21          should be the 15 nanometer node.

